

TO-92 Plastic-Encapsulate Transistors

A92H331

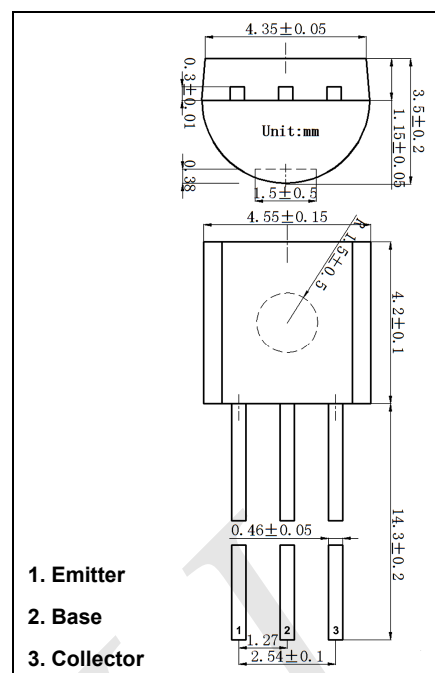
PNP Transistors

Features

- High voltage

Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector Base Voltage	-310	V
V _{CEO}	Collector Emitter Voltage	-305	V
V _{EBO}	Emitter Base Voltage	-5	V
I _C	Collector Current -Continuous	-200	mA
I _{CM}	Collector Current –Pulsed	-500	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C
R _{θJA}	Thermal Resistance, Junction - Ambient	200	°C/mW
R _{θJC}	Thermal Resistance, Junction - Case	83.3	°C/mW



Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C = -100μA, I _E = 0	-310			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -1mA, I _B = 0	-305			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = -100μA, I _C = 0	-5			V
I _{CBO}	Collector cut-off current	V _{CB} = -200V, I _E = 0			-0.25	μA
I _{EBO}	Emitter cut-off current	V _{EB} = -5V, I _C = 0			-0.1	μA
h _{FE(1)}	DC current gain	V _{CE} = -5V, I _C = -1mA	100			
h _{FE(2)}		V _{CE} = -5V, I _C = -10mA	60			
h _{FE(3)}		V _{CE} = -10V, I _C = -1mA	60			
h _{FE(4)}		V _{CE} = -10V, I _C = -10mA	100		200	
h _{FE(5)}		V _{CE} = -10V, I _C = -80mA	60			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = -20mA, I _B = -2mA			-0.2	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C = -20mA, I _B = -2mA			-0.9	V
f _T	Transition frequency	V _{CE} = -20V, I _C = -10mA, f = 30MHz	50			MHz

Classification OF h_{FE(1)}

Rank	A	B
Range	100 - 150	150 - 200

Typical Characteristics

